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IN THE CLAIMS

1. (Currently Amended) An etching method comprising:

providing a wafer having a dielectric layer and plurality of electrodes separated from each other;

planarizing the electrodes and the dielectric layer such that top surfaces of the electrodes are coplanar with the top surface of the dielectric layer;

after planarizing the electrodes and the dielectric layer, wet etching the wafer including the dielectric layer and separated electrodes such that at least one of the electrodes partially protrudes from the top surface of the dielectric layer;

~~providing a wafer having a dielectric layer and a plurality of electrodes separated from each other, wherein at least one of the plurality of electrodes partially protrudes from a top surface of the dielectric layer;~~

etching the dielectric layer with a chemical solution; and

prior to etching the dielectric layer, reducing the protruding portion of the electrode, wherein reducing the protruding portion includes recessing a top surface of the electrode at least 500 angstroms below the top surface of the dielectric layer.

2. (Original) The method of claim 1, wherein the protruding portion of the electrode is reduced sufficiently to prevent any bubbles included in the chemical solution from adhering to the electrode.

3-6. (Canceled)

7. (Original) The method of claim 1, wherein reducing the protruding portion comprises dry etching.

8. (Original) The method of claim 7, wherein drying etching uses an etchant selected from the group consisting of HB_4, Cl_2, CF_4, C_4F_8, C_5F_8, SF_6, O_2 and combinations thereof.

9. (Original) The method of claim 1, wherein reducing the protruding portion comprises wet etching.